Table S1

Calculated binding energy (E_b) , cohesive energy (E_{coh}) , the distance (d) between g-C₃N₄ and C₃N

layer for different stacked patterns.

	AA1	AA2	AB1	AB2	AB3
$E_b(eV)$	-1.021	-1.166	-1.212	-1.143	-1.188
$E_{coh}(eV)$	-2.965	-2.978	-2.982	-2.976	-2.980
<i>d</i> (Å)	3.259	2.890	2.988	2.968	2.969



Fig.S1 Projected band structure of g-C₃N₄/C₃N vdWH at HSE06 level.



Fig.S2 Band alignments of g-C₃N₄/C₃N vdWH at HSE06 level.



Fig.S3 Projected band structures of $g-C_3N_4/C_3N$ vdWH under the in-plane biaxial strains.



Fig.S4 Projected band structures of g-C₃N₄/C₃N vdWH under different E_{field}.



Fig.S5 Three sites of Ti atom at $g-C_3N_4/C_3N$ vdWH.



Fig.S6 Band structures of metal atoms adsorbed on $g-C_3N_4$ surface of $g-C_3N_4/C_3N$ vdWH.



Fig.S7 Band structures of metal atoms adsorbed on C_3N surface of g- C_3N_4/C_3N vdWH.



Fig.S8 Band structures of metal atoms embedded into the interlayer of $g-C_3N_4/C_3N$ vdWH.